In the Specification

Please amend paragraph 0046 as follows:

[0046] Referring to Fig. 7, layers 212, 214, 216, 218, 220 and 222 are formed over substrate 204. Layers 212, 214, 216, 218, 220 and 222 can ultimately be utilized to form the layers 18, 42, 46, 60, 48, and 62~~, 50 and 64~~, respectively. Accordingly, layer 212 comprises a soft magnetic material ultimately utilized to form part of a sense layer, while layer 216 also comprises a soft magnetic material that is utilized to form a reference layer. Layer 220, in contrast, comprises a hard magnetic material utilized to form a pinning layer. Layer 222 can comprise a material which protects layer 220, and which is selectively etchable relative to layer 220, such as, for example, titanium nitride in applications in which the antiferromagnetic layer 220 comprises one or more of the materials of NiCoO, MnFe, TbCo, or MnNi, (with the listed materials being shown in terms of primary chemical constituents, rather than the stoichiometric ratios of such constituents). Layers corresponding to layers 50 and 64 can be formed over layer 222 in aspects of the invention which are not shown.

Please amend paragraph 0053 as follows:

[0053] Fig. 11 shows a diagrammatic, cross-sectional view of a portion of the wafer portion of Fig. 10 along the line 11-11, and corresponds to a view utilized in Figs. 3-8. Wordline 14 can be seen to comprise a pinning layer 72 and a conductive layer 70, as described above with reference to Figs. 1 and 2. Further, the construction of Fig. 11 can be seen to correspond ~~identically~~ to ~~that~~ a structure similar to that described with reference to Fig. 2, with the materials 208 and 210 corresponding to materials 20 and 16 of Fig. 2, and layers 212, 214, 216, 218, 220 and 222 corresponding to layers 18, 42, 46, 60, 48, and 62~~, 50 and 64~~, respectively. Additional layers corresponding to the layers 50 and 64 of the Fig. 2 structure can be formed over the layer 222 of Fig. 11 so that the construction of Fig. 11 corresponds identically to the construction of Fig. 2.